

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Inventors: John F. Conley, Jr., and Yoshi Ono

Serial No: Not Yet Assigned

Filed: Herewith

Title: METHOD TO CONTROL THE
INTERFACIAL LAYER FOR
DEPOSITION OF HIGH
DIELECTRIC CONSTANT FILMS

PATENT APPLICATION

Attorney Docket No.
SLA0778

Hon. Commissioner for Patents
Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Sir:

Listed on attached Form PTO-1449 is information submitted pursuant to
37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by
the Examiner and made of record in the above-identified application.

September 30, 2003
(Date)

Respectfully submitted,



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FORM PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION				DOCKET NUMBER SLA0778		APPLICATION NUMBER	
				APPLICANT John F. Conley, Jr., and Yoshi Ono			
				FILING DATE: September 30, 2003		GROUP ART UNIT	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILE. DATE IF APPROP.	
FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER	DATE	COUNTRY/NAME	CLASS	SUB CLASS	TRANSLATION YES NO	
OTHER DOCUMENTS							
	Article entitled: Nucleation and interface formation mechanisms in atomic layer deposition of gate oxides; by Frank and Chabal, published in Applied Physics Letters, vol 82, No. 26, 30 June 2003						
	Article entitled: Enhanced initial growth of atomic-layer-deposited metal oxidized on hydrogen-terminated silicon; by Frank and Chabal, published in Applied Physics Letters, vol 83, No. 4, 28 July 2003						
	Article entitled: Nucleation and growth of atomic layer deposited HfO ₂ gate dielectric layers on chemical oxide (Si-O-H) and thermal oxide (SiO ₂ or Si-O-N) underlayers; by Green <i>et al.</i> , published in Journal of Applied Physics, vol. 92, No. 12, 15 December 2002						
	Article entitled: Atomic Layer Deposition of Hafnium Oxide Using Anhydrous Hafnium Nitrate; by Conley <i>et al.</i> , published in Electrochemical and Solid-State Letters, available electronically February 26, 2002						
	Article entitled: Atomic layer deposition of thin hafnium oxide films using a carbon free precursor; by Conley and Solanki, published in Journal of Applied Physics, vol. 93, No. 1, 1 January 2003						
EXAMINER				DATE CONSIDERED			